EAST - [10663710 self-aligned trench gate.wsp: 1]

File View Edit Tools Window Help

- Drafts
  - BRS:
  - BRS:
  - BRS:
  - BRS: knall
  - BRS: 19 21 23
  - BRS: 32with 33
- Pending
- Active
  - L1: (8152) ((trench$2 recess$4)) near2 gate
  - L2: (28943) self adj aligned
  - L3: (0) 10/663710
  - L4: (139) 2 near3 1
  - L5: (2816) (insulat$5 dielectric oxide) near (column pillar)
  - L6: (0) 4 same 5
  - L8: (1) 4 and 5
  - L7: (4) 1 same 5
  - L9: (1) 5 and 4
  - L10: (341) (257/332).CCLS.
  - L11: (2) 10 and 5
  - L12: (980) (257/330).CCLS.
  - L13: (14) 12 and 5
- Failed
- Saved
  - (1) 09/948877
  - (1736) "KONINKLIJKE PHILIPS".as.
  - (1) 10/663710

Search | Edit | Browse | Queue | Clear

DBs | USPAT; US PGPUB; EPO; JPO; DERWENT; IBM_TDB | Plurals

Default operator: OR | Highlight all hit terms initially

12 and 5

Aug 2004

Hit List | Hit Table | Image | Text | HTML

	U	T	Inventor	Document I	Issue	P	Title	Current	CurrentXR	Retrieval	S	C	P	2	3	4	5	Image Doc.	P
1			Inagawa, Hir	US 2002011	20020	2	Insulated gate type semiconductor device an	438/270	257/330;									US 200201	
2			Noble, Wend	US 2001002	20011	2	Circuits and methods using vertical, complem	257/330										US 200100	
3			Noble, Wend	US 6777744	20040	2	Circuits and methods using vertical, complem	257/330	438/199;									US 677774	
4			Madson, Gor	US 6576954	20030	1	Trench MOSFET formed using selective epit	257/330	257/E21.41									US 657695	
5			Furukawa, T	US 6440801	20020	7	Structure for folded architecture pillar mem	438/272	257/302;									US 644080	
6			Noble, Wend	US 6242775	20010	2	Circuits and methods using vertical complem	257/330	257/351;									US 624277	
7			Furukawa, T	US 6114725	20000	7	Structure for folded architecture pillar mem	257/330	257/296;									US 611472	
8			Burns, Jr., St	US 5990509	19991	6	2F-square memory cell for gigabit memory ap	257/296	257/316;									US 599050	
9			Park, Kyu-ch	US 5612559	19970	1	Semiconductor device having pillar-shaped tr	257/302	257/301;									US 561255	
10			Shah, Pradee	US 5508544	19960	1	Three dimensional FAMOS memory devices	257/316	257/321;									US 550854	

Title | Details | HTML

Ready

NUM